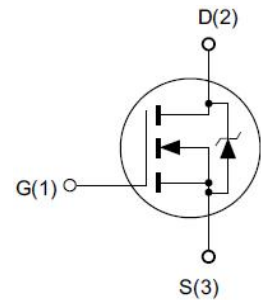
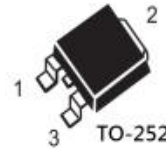


Features

- ◆ 800V, 8A, $R_{DS(ON)}(Typ.) = 0.62\Omega @ V_{GS} = 10V$
- ◆ Advanced Super junction Technology
- ◆ Easy to control Gate switching
- ◆ 100% Avalanche Tested

Application

- ◆ PC power, PD Adaptor
- ◆ LCD & PDP TV and LED lighting
- ◆ Single-ended flyback or two-transistor forward topologies



Absolute Maximum Ratings $T_c = 25^\circ \text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-Source Voltage ^a	800	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ \text{C}$	8	A
I_{DM}	Drain Current-Pulsed ^b	24	A
P_D	Maximum Power Dissipation, $T_c = 25^\circ \text{C}$	113.6	W
dv/dt	Peak Diode Recovery dv/dt ^c	4	V/ns
E_{AS}	Single Pulsed Avalanche Energy ^d	88	mJ
T_J, T_{STG}	Operating and Store Temperature Range	150, -55 to 150	$^\circ \text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.1	$^\circ \text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	$^\circ \text{C/W}$

Electrical Characteristics $T_J = 25^\circ \text{C}$ unless otherwise noted

■ Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	800	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	-	-	1.0	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.8	-	4.2	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^c	$V_{GS} = 10V, I_D = 6.0A$	-	0.62	0.75	Ω

■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
R_G	Gate Resistance	$f = 1.0MHz$	-	25	-	Ω
C_{iss}	Input Capacitance	$V_{DS} = 100V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	-	850.8	-	pF
C_{oss}	Output Capacitance		-	34.4	-	pF
C_{rss}	Reverse Transfer Capacitance		-	0.92	-	pF

■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400V,$ $I_D = 4.1A,$ $V_{GS} = 10V,$ $R_G = 50\Omega$	-	40.6	-	ns
t_r	Turn-On Rise Time		-	34.8	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	128	-	ns
t_f	Turn-Off Fall Time		-	31	-	ns
Q_g	Total Gate Charge	$V_{DS} = 400V,$ $I_D = 4.1A,$ $V_{GS} = 0 \text{ to } 10V$	-	18.5	-	nC
Q_{gs}	Gate-Source Charge		-	5.0	-	nC
Q_{gd}	Gate-Drain Charge		-	6.6	-	nC

■ Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	8	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	24	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_F = 1A$	-	0.75	-	V
T_{rr}	Body Diode Reverse Recovery Time	$I_F = 4.1A, V_R = 400V$ $dl_F/dt = 100A/\mu s$	-	266.5	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F = 4.1A, V_R = 400V$ $dl_F/dt = 100A/\mu s$	-	2.2	-	μC

Notes:

- $T_J = +25^\circ C$ to $+150^\circ C$.
- Repetitive rating: pulse width limited by maximum junction temperature.
- Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- $L = 10mH, V_{DD} = 50V, I_{AS} = 4.2A, R_G = 25\Omega$ Starting $T_J = 25^\circ C$.

■ Characteristic Curve

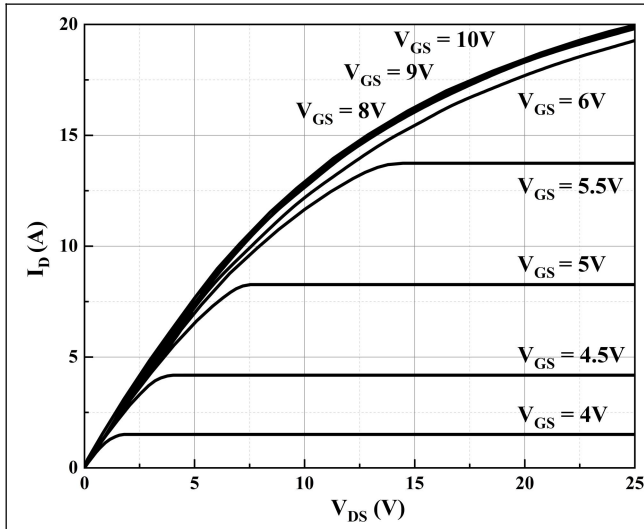


Figure 1. Typical Output Characteristics

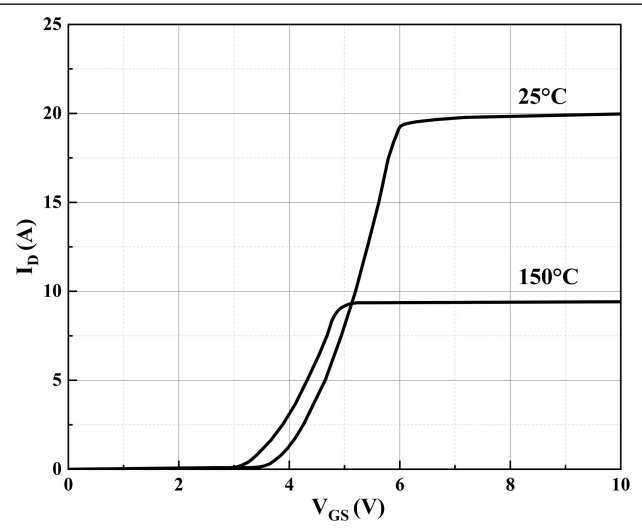


Figure 2. Typical Transfer Characteristics

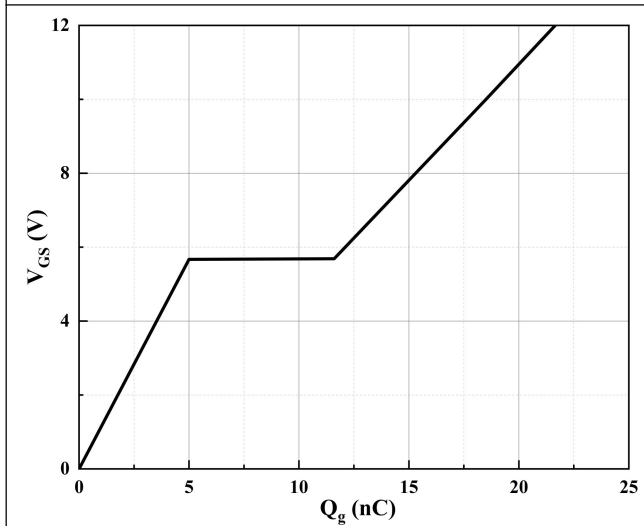


Figure 3. Typical Gate-Charge Characteristics

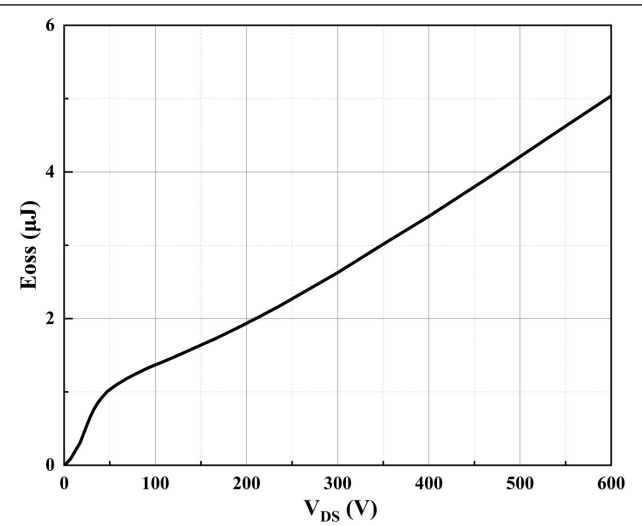


Figure 4. Typical Coss stored energy

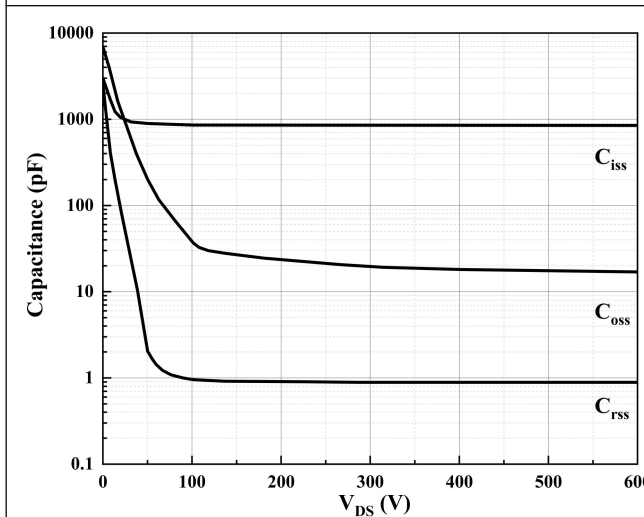


Figure 5. Capacitance Characteristics

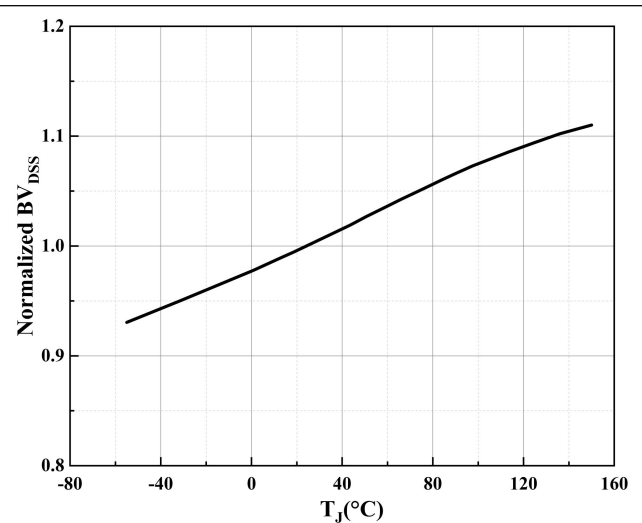


Figure 6. Normalized Breakdown voltage vs Junction Temperature

■ Characteristic Curve

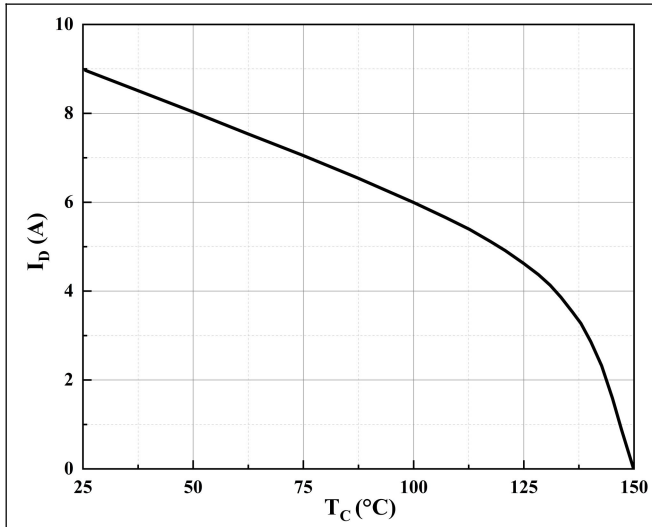


Figure 7. Maximum Continuous Drain Current vs Case Temperature

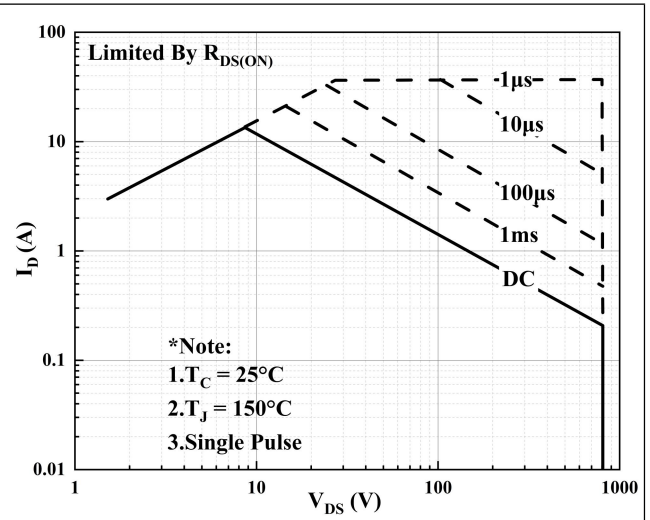


Figure 8. Safe operating area

■ Package Information

TO-252

